Unisys

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TO: S Hull/562

FROM: K. Sahu/S. Kniffin/300.1

SUBJECT: Radiation Report on AMP-01A (Analog Devices) (LDC 9818)

PROJECT: IRAC

cc: R. Williams/722.0, R. Reed/562, A. Sharma/562, OFA Library/300.1

A radiation evaluation was performed on AMP-01A (5962-8863001VA) Low Noise Precision Instrumentation Amplifier (Analog Devices) to determine the total ionizing dose (TID) tolerance of these parts. The TID testing was performed using a Co⁶⁰ gamma ray source. During the radiation testing, eight parts were irradiated under bias (see Figure 1 for bias configuration) and two parts were used as control samples. The TID radiation levels were 2.5, 5.0, 10.0, 15.0, 20.0, 30.0, and 50.0kRads.¹ The dose rate was 0.060kRads/hour (0.02Rads/s). See Table II for the radiation schedule and effective dose rate calculation. After the 10.0 and 50.0kRad irradiations, the parts were annealed under bias at 25°C and tested after 288 and 168 hours respectively.² After each radiation exposure and annealing treatment, parts were electrically tested according to the test conditions and the specification limits³ listed in Table III.

An executive summary of the test results is provided below in bold, followed by a detailed summary of the test results after each radiation level and annealing step. For detailed information, refer to Tables I through IV and Figure 1.

All parts passed all tests initially and upon irradiation to 5kRads. After the 10 and 15kRad irradiations, most parts showed marginal degradation in Voos. From the 20 to 50kRad irradiations, most parts showed some degradation in Gain_err_100x and continued degradation in Voos. After the 50kRad irradiation, two parts showed some degradation in Gain_err_1x. After annealing the parts for 168 hours at 25°C, all parts showed significant recovery in Gain_err_1x, Gain_err_100x and Voos. No significant change was noted in any other parameters.

Initial electrical measurements were made on 10 samples. Eight samples (SN's 13, 14, 15, 16, 17, 18, 19, and 20) were used as radiation samples while SN's 11 and 12 were used as control samples. All parts passed all tests during initial electrical measurements.

All parts passed all tests up to 5kRads.

After the 10kRad irradiation, five parts marginally exceeded the specification limit of 3.0mV for Voos with readings in the range of 5.1 to 8.8mV. **All parts passed all other tests.**

After annealing the parts for 288 hours at 25°C, the five parts showed modest recovery in Voos with readings in the range of 3.29 to 6.19mV.

After the 15kRad irradiation, six parts exceeded the specification limit for Voos with readings in the range of 4.50 to 14.15mV. **All parts passed all other tests.**

¹ The term Rads, as used in this document, means Rads (silicon). All radiation levels cited are cumulative.

² The temperature 25°C as used in this document implies room temperature.

³ These are manufacturer's pre-irradiation data specification limits. The manufacturer provided no post-irradiation limits at the time these tests were performed.

After the 20kRad irradiation, all parts exceeded the specification limit for Voos with readings in the range of 5.4 to 27.4mV. Seven parts exceeded the specification limit of 0.60% for Gain_err_100x with readings in the range of 0.68 to 1.90%. All parts passed all other tests.

After the 30kRad irradiation, six parts exceeded the specification limit for Voos with readings in the range of 9.5 to 44mV. All parts exceeded the specification limit for Gain_err_100x with readings in the range of 0.65 to 1.37%. **All parts passed all other tests.**

After the 50kRad irradiation, all parts exceeded the specification limit for Voos with readings in the range of 5.7 to 65mV. Two parts marginally exceeded the specification limit of 0.60% for Gain_err_1x with readings of 0.92 and 1.00%. Six parts exceeded the specification limit for Gain_err_100x with readings in the range of 0.73 to 1.63%. **All parts passed all other tests.**

After annealing the parts for 168 hours at 25°C, the parts showed significant recovery in Gain_err_1x and Gain_err_100x with only one part marginally exceeding the specification limit for Gain_err_100x with a reading of 0.62%. Modest recovery was noted in Voos although all parts exceeded the specification limit with readings in the range of 3.6 to 32.1mV. No significant change was noted in any other parameter.

Table IV provides a summary of the test results with the mean and standard deviation values for each parameter after each irradiation exposure and annealing step.

Any further details about this evaluation can be obtained upon request. If you have any questions, please call us at (301) 731-8954.

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+IN 18 V_{IOS} NULL 17 3 V_{IOS} NULL -IN 4 V_{oos} NULL 15 $R_{\rm s}$ 14 V_{oos} NULL R_s 6 Test Pin 13 OUT 7 SENSE 12 V+ 8 REFERENCE 11 V-9 OUTPUT 10

Figure 1. Radiation Bias Circuit for AMP-01A

Notes:

- 1. $+V = +18.0V \pm 0.5V$, $-V = -18.0V \pm 0.5V$.
- 2. $R = 10k\Omega \pm 5\%$, $\frac{1}{4}W$.

TABLE I. Part Information

Generic Part Number: AMP-01A

IRAC Part Number: AMP-01A (5962-8863001VA)

Charge Number: M99715

Manufacturer: Analog Devices

Lot Date Code (LDC): 9818

Quantity Tested: 10

Serial Number of Control Samples: 11, 12

Serial Numbers of Radiation Samples: 13, 14, 15, 16, 17, 18, 19, and 20

Part Function: High Precision Voltage Reference

Part Technology: Bipolar

Package Style: 18 Pin DIP

Test Equipment: A540

Test Engineer: S. Norris

• The manufacturer for this part guaranteed no radiation tolerance/hardness.

TABLE II. Radiation Schedule for AMP-01A EVENT......DATE 10) 168 HOUR ANNEALING @25°C01/11/98

PARTS WERE IRRADIATED AND ANNEALED UNDER BIAS, SEE FIGURE 1.

Effective Dose Rate = 50,000 RADS/35 DAYS=59.5 RADS/HOUR=0.02 RADS/SEC

Table III. Electrical Characteristics of AMP-01A /1

Test									
#	Parameter	Units	Test Conditions /2 /3	min	max				
1	Icc	mA	No Load		4.80				
2	Iss	mA	No Load	-4.80					
3	Vios	nV		-50	50				
4	+swing	\mathbf{V}	$\mathbf{R_L} = 2\mathbf{k}\mathbf{W}$	13.0					
5	-swing	\mathbf{V}	$\mathbf{R_L} = 2\mathbf{k}\mathbf{W}$		-13.0				
6	slew rate	V/ms	$\mathbf{A}\mathbf{v} = 10$	3.500					
7	+psrr_Av_1	dB	Gain = 1, +Vcc = 5V to 15V	75					
8	-psrr_Av_1	dB	Gain = 1 , $+Vcc = -5V$ to $-15V$	50					
9	+psrr_Av_10	dB	Gain = 10, +Vcc = 5V to 15V	95					
10	-psrr_Av_10	dB	Gain = 10 , $+Vcc = -5V$ to $-15V$	70					
11	+psrr_Av_100	dB	Gain = 100 , $+Vcc = 5V$ to $15V$	110					
12	-psrr_Av_100	dB	Gain = 100 , $+Vcc = -5V$ to $-15V$	90					
13	+psrr_Av_1k	dB	Gain = 1000 , $+Vcc = 5V$ to $15V$	120					
14	-psrr_Av_1k	dB	Gain = 1000 , $+Vcc = -5V$ to $-15V$	105					
15	cmrr_Av_1	dB	$Gain = 1, V_{CM} = \pm 10.0V$	80					
16	cmrr_Av_10	dB	Gain = 10, $V_{CM} = \pm 10.0V$	95					
17	cmrr_Av_100	dB	Gain = 100, $V_{CM} = \pm 10.0V$	115					
18	+Ibias	nA		-4.00	4.00				
19	-Ibias	nA		-4.00	4.00				
20	Ios	nA	(Calculated)	1.00	1.00				
21	Gain_err_1x	%	Bench Test		0.6				
22	Gain_err_100x	%	Bench Test		0.6				
23	Voos	mV	Bench Test		3.00				

Notes:

1/ These are the manufacturer's non-irradiated data sheet specification limits. The manufacturer provided no post-irradiation limits at the time the tests were performed.

 $2/V_S = \pm 15V$, $R_S = 10k\Omega$, $R_L = 2k\Omega$, and $T_A = 25^{\circ}C$ unless otherwise specified.

3/ CMRR_1k not performed due to system gain of 10 million.

TABLE IV: Summary of Electrical Measurements after Total Dose Exposures and Annealing for AMP-01A /1

							Total Dose Exposure (kRads Si) Annealing							aling	Total Dose Exposure (kRads Si)									Annealing	
					Ini	itial	2.5		5.0		10.0		288 hou	rs	15.0 20.0		20.0	30.0			50.0		168 hours		
Test			Spec. 1	Lim. /2									@25°C										@25°C		
#	Parameters	Units	min	max	mean	sd	mean	sd	mean	sd	mean	sd	mean	sd	mean	sd	mean	sd	mean	sd	mean	sd	mean	sd	
1	Icc	mA		4.80	3.60	0.10	3.61	0.12	3.60	0.11	3.64	0.11	3.51	0.19	3.51	0.13	3.12	0.10	3.55	0.17	3.56	0.19	3.54	0.18	
2	Iss	mA	-4.80		-3.58	0.11	-3.59	0.12	-3.59	0.11	-3.63	0.11	-3.82	0.20	-3.84	0.13	-3.43	0.10	-3.88	0.18	-3.88	0.19	-3.86	0.18	
3	Vios	?V	-50	50	-19	1	-16	1	-14	1	-9	1	32	0.3	32	0.3	32	0.3	33	0.6	32	1	33	1	
4	+swing	V	13.0		13.8	0.1	13.8	0	13.8	0.2	13.9	0	13.9	0	13.9	0	13.9	0	13.9	0	13.9	0	13.9	0	
5	-swing	V		-13.0	-14.2	0	-14.2	0	-14.1	0	-14.2	0	-13.8	0	-14.3	0	-14.3	0.1	-14.5	0.1	-14.3	0	-14.3	0	
6	slew rate	V/?s	3.500		5.044	0.736	5.012	0.914	4.703	0.656	5.087	0.710	6.441	0.282	6.575	0.199	5.825	0.179	5.625	0.171	6.715	0.217	6.685	0.256	
7	+psrr_Av_1	dB	75		140	0.3	140	0.3	140	0.3	140	0.2	146	10	147	7	140	0	139	2	143	5	142	5	
8	-psrr_Av_1	dB	50		120	0	120	0	120	0	120	0	142	5	144	6	140	0	142	7	141	6	140	6	
9	+psrr_Av_10	dB	95		140	0.4	140	0.4	140	0.2	140	0.3	140	1	140	1	140	0	140	0	140	1	140	0	
10	-psrr_Av_10	dB	70		120	0	120	0	120	0	120	0	140	0	140	1	140	0	140	1	140	1	140	0	
11	+psrr_Av_100	dB	110		140	0.2	140	0.2	140	0.3	140	0.2	140	0	140	0	140	1	140	0	140	0	140	0	
12	-psrr_Av_100	dB	90		120	0	120	0	120	0	120	0	140	0	140	0	140	1	140	0	140	0	140	0	
13	+psrr_Av_1k	dB	120		140	0.2	140	0.2	140	0.3	140	0.2	140	0	140	0	140	0	140	0	140	0	140	0	
14	-psrr_Av_1k	dB	105		120	0	120	0	120	0	120	0.1	140	0	140	0	140	0	140	0	140	0	140	0	
15	cmrr_Av_1	dB	80		119	0	119	0	119	0	119	0.1	152	9	150	6	157	9	146	9	151	7	147	9	
16	cmrr_Av_10	dB	95		119	0.1	119	0.1	119	0	119	0	155	6	153	5	162	11	154	3	153	4	156	11	
17	cmrr_Av_100	dB	115		119	0	119	0	119	0	119	0.1	153	1	154	3	155	6	155	4	156	4	156	4	
18	+Ibias	nA	-4.00	4.00	0.18	0.26	0.52	0.36	0.06	0.28	0.15	0.19	0.46	0.29	0.62	0.21	-0.36	0.77	0.62	0.33	1.21	0.52	0.23	0.41	
19	-Ibias	nA	-4.00	4.00	0.03	0.01	-0.03	0.03	0.14	0.06	0.16	0.17	0.13	0.20	0.17	0.13	0.53	0.08	1.12	0.32	2.35	0.32	1.56	0.27	
20	Ios	nA	1.00	1.00	0.18	0.26	0.53	0.35	0.00	0.28	0.08	0.15	0.41	0.27	0.59	0.17	-0.57	0.78	0.18	0.35	0.27	0.51	-0.40	0.37	
21	Gain_err_1x	%		0.60	0.22	0.04	0.23	0.04	0.24	0.04	0.28	0.04	0.25	0.04	0.28	0.03	0.28	0.04	0.38	0.05	0.53	0.26	0.38	0.05	
22	Gain_err_100x	%		0.60	0.12	0.08	0.27	0.10	0.37	0.04	0.28	0.14	0.39	0.07	0.59	0.40	1.34	0.48	0.93	0.21	0.93	0.38	0.51	0.09	
23	Voos	mV		3.00	1.26	0.51	1.47	0.74	1.96	1.27	5.10	2.25	3.35	1.55	7.34	5.30	11.93	6.79	22.04	16.86	26.60	16.35	15.78	8.95	

Notes:

Radiation sensitive parameters: Voos.

^{1/} The mean and standard deviation values were calculated over the eight parts irradiated in this testing. The control samples remained constant throughout testing and are not included in this table.

^{2/} These are manufacturer's pre-irradiation data sheet specification limits. No post-irradiation limits were provided by the manufacturer at the time the tests were performed.